

Amendments to Claims:

4. (currently amended) A method of manufacturing a device having an elevated holding voltage, and formed in a semiconductor material of a first conductivity type, the semiconductor material having a dopant concentration, the device comprising
 - a well of a second conductivity type formed in the semiconductor material, the well having a dopant concentration;
 - a first region of the second conductivity type formed in the well, the first region having a dopant concentration greater than the dopant concentration of the well, the first region being connected to a first node;
 - a second region of the first conductivity type formed in the well, the second region having a dopant concentration greater than the dopant concentration of the semiconductor material, the second region being connected to the first node;
 - a third region of the second conductivity type formed in the semiconductor material, the third region having a dopant concentration greater than the dopant concentration of the well, the third region being connected to a second node, and
 - a fourth region of the first conductivity type formed in the semiconductor material, the fourth region having a dopant concentration greater than the dopant concentration of the semiconductor material, and being connected to the second node, the method comprising
 - adjusting the size of the second region to limit injection of minority carriers to achieve the desired elevated holding voltage.
5. (previously presented) The method of claim 4, wherein the first conductivity type is p type and the second conductivity type is n type.
6. (original) The method of claim 5, wherein, in addition to adjusting the size of the second region, adjusting the size of the third region to increase electron injection to a point where space charge neutralization is sufficiently limited to achieve the desired elevated holding voltage.